

# MOSFET – N-Channel, POWERTRENCH®

20 V, 9 A, 18 mohm

## FDME820NZT

### General Description

This Single N-Channel MOSFET has been designed using onsemi's advanced Power Trench process to optimize the  $R_{DS(ON)}$  @  $V_{GS} = 1.8\text{ V}$  on special MicroFET™ leadframe.

### Features

- Max  $R_{DS(ON)} = 18\text{ m}\Omega$  at  $V_{GS} = 4.5\text{ V}$ ,  $I_D = 9\text{ A}$
- Max  $R_{DS(ON)} = 24\text{ m}\Omega$  at  $V_{GS} = 2.5\text{ V}$ ,  $I_D = 7.5\text{ A}$
- Max  $R_{DS(ON)} = 32\text{ m}\Omega$  at  $V_{GS} = 1.8\text{ V}$ ,  $I_D = 7\text{ A}$
- Low Profile – 0.55 mm maximum – in the New Package MicroFET 1.6x1.6 Thin
- HBM ESD Protection Level > 2.5 kV (Note 3)
- Free from Halogenated Compounds and Antimony Oxides
- RoHS Compliant

### Applications

- Li-Ion Battery Pack
- Baseband Switch
- Load Switch
- DC-DC Conversion

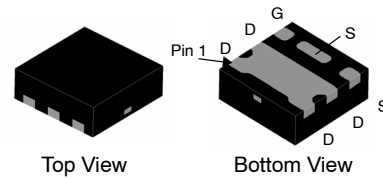
### MOSFET MAXIMUM RATINGS ( $T_A = 25^\circ\text{C}$ , unless otherwise noted)

Symbol	Parameter	Ratings	Unit
$V_{DS}$	Drain to Source Voltage	20	V
$V_{GS}$	Gate to Source Voltage	$\pm 12$	V
$I_D$	Drain Current – Continuous $T_A = 25^\circ\text{C}$ (Note 1a) – Pulsed	9 40	A
$P_D$	Power Dissipation for Single Operation $T_A = 25^\circ\text{C}$ (Note 1a) $T_A = 25^\circ\text{C}$ (Note 1b)	2.1 0.7	W
$T_J, T_{STG}$	Operating and Storage Junction Temperature Range	-55 to +150	$^\circ\text{C}$

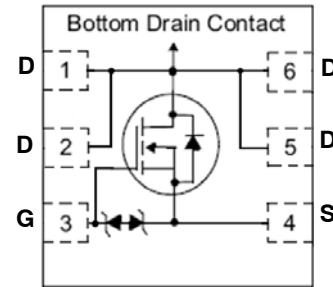
Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

### THERMAL CHARACTERISTICS

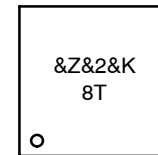
Symbol	Parameter	Ratings	Unit
$R_{\theta JA}$	Thermal Resistance, Junction to Ambient (Note 1a)	70	$^\circ\text{C}/\text{W}$
$R_{\theta JA}$	Thermal Resistance, Junction to Ambient (Note 1b)	190	



MicroFET  
(UDFN6)  
CASE 517DV



### MARKING DIAGRAM



&Z = Assembly Plant Code  
&2 = 2-Digit Date Code  
&K = 2-Digits Lot Run Traceability Code  
8T = Specific Device Code

### ORDERING INFORMATION

Device	Package	Shipping†
FDME820NZT	UDFN6 (Pb-Free)	5000 / Tape & Reel

†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specification Brochure, [BRD8011/D](#).

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## ELECTRICAL CHARACTERISTICS (T<sub>J</sub> = 25°C unless otherwise noted)

Symbol	Parameter	Test Condition	Min	Typ	Max	Unit
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### OFF CHARACTERISTICS

BV <sub>DSS</sub>	Drain to Source Breakdown Voltage	I <sub>D</sub> = 250 μA, V <sub>GS</sub> = 0 V	20	–	–	V
$\frac{\Delta BV_{DSS}}{\Delta T_J}$	Breakdown Voltage Temperature Coefficient	I <sub>D</sub> = 250 μA, Referenced to 25°C	–	20	–	mV/°C
I <sub>DSS</sub>	Zero Gate Voltage Drain Current	V <sub>DS</sub> = 16 V, V <sub>GS</sub> = 0 V	–	–	1	μA
I <sub>GSS</sub>	Gate to Source Leakage Current	V <sub>GS</sub> = ±12 V, V <sub>DS</sub> = 0 V	–	–	±10	μA

### ON CHARACTERISTICS

V <sub>GS(th)</sub>	Gate to Source Threshold Voltage	V <sub>GS</sub> = V <sub>DS</sub> , I <sub>D</sub> = 250 μA	0.5	0.8	1.0	V
$\frac{\Delta V_{GS(th)}}{\Delta T_J}$	Gate to Source Threshold Voltage Temperature Coefficient	I <sub>D</sub> = 250 μA, Referenced to 25°C	–	–3	–	mV/°C
R <sub>DS(on)</sub>	Drain to Source On-Resistance	V <sub>GS</sub> = 4.5 V, I <sub>D</sub> = 9 A V <sub>GS</sub> = 2.5 V, I <sub>D</sub> = 7.5 A V <sub>GS</sub> = 1.8 V, I <sub>D</sub> = 7 A, V <sub>GS</sub> = 4.5 V, I <sub>D</sub> = 9 A, T <sub>J</sub> = 125°C	–	14	18	mΩ
			–	17	24	
			–	26	32	
			–	19	24	

### DYNAMIC CHARACTERISTICS

C <sub>iss</sub>	Input Capacitance	V <sub>DS</sub> = 10 V, V <sub>GS</sub> = 0 V, f = 1 MHz	–	865	–	pF
C <sub>oss</sub>	Output Capacitance		–	203	–	pF
C <sub>rss</sub>	Reverse Transfer Capacitance		–	190	–	pF
R <sub>g</sub>	Gate Resistance	f = 1 MHz	–	1.0	–	Ω

### SWITCHING CHARACTERISTICS

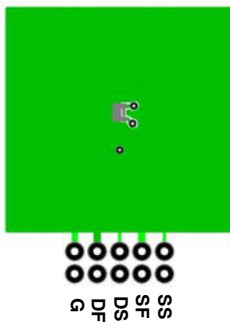
t <sub>d(on)</sub>	Turn-On Delay Time	V <sub>DD</sub> = 10 V, I <sub>D</sub> = 4 A, V <sub>GS</sub> = 4.5 V, R <sub>GEN</sub> = 2 Ω	–	9	–	ns
t <sub>r</sub>	Turn-On Rise Time		–	5	–	ns
t <sub>d(off)</sub>	Turn-Off Delay Time		–	19	–	ns
t <sub>f</sub>	Turn-Off Fall Time		–	5	–	ns
Q <sub>g</sub>	Total Gate Charge	V <sub>DD</sub> = 4.2 V, I <sub>D</sub> = 3 A, V <sub>GS</sub> = 4.3 V	–	8.0	–	nC
Q <sub>g</sub>	Total Gate Charge	V <sub>DD</sub> = 4.2 V, I <sub>D</sub> = 3 A, V <sub>GS</sub> = 4.5 V	–	8.5	–	nC
Q <sub>gs</sub>	Gate to Source Gate Charge	V <sub>DD</sub> = 10 V, I <sub>D</sub> = 9 A	–	1.4	–	nC
Q <sub>gd</sub>	Gate to Drain "Miller" Charge		–	3.2	–	nC

### DRAIN-SOURCE CHARACTERISTICS

V <sub>SD</sub>	Source to Drain Diode Forward Voltage	V <sub>GS</sub> = 0 V, I <sub>S</sub> = 1.6 A (Note 2) V <sub>GS</sub> = 0 V, I <sub>S</sub> = 9 A (Note 2)	–	0.7 0.8	1.2 1.2	V
t <sub>rr</sub>	Reverse Recovery Time	I <sub>F</sub> = 9 A, di/dt = 100 A/μs	–	18	–	ns
Q <sub>rr</sub>	Reverse Recovery Charge		–	4	–	nC

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

- R<sub>θJA</sub> is determined with the device mounted on a 1 in<sup>2</sup> oz. copper pad on a 1.5 x 1.5 in. board of FR-4 material. R<sub>θJC</sub> is guaranteed by design while R<sub>θJA</sub> is determined by the user's board design.



a. 70°C/W when mounted on a 1 in<sup>2</sup> pad of 2 oz copper.



b. 190°C/W when mounted on a minimum pad of 2 oz copper.

- Pulse Test: Pulse Width < 300 μs, Duty Cycle < 2.0%.
- The diode connected between the gate and source serves only as protection against ESD. No gate overvoltage rating is implied.

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## TYPICAL CHARACTERISTICS ( $T_J = 25^\circ\text{C}$ , unless otherwise noted)

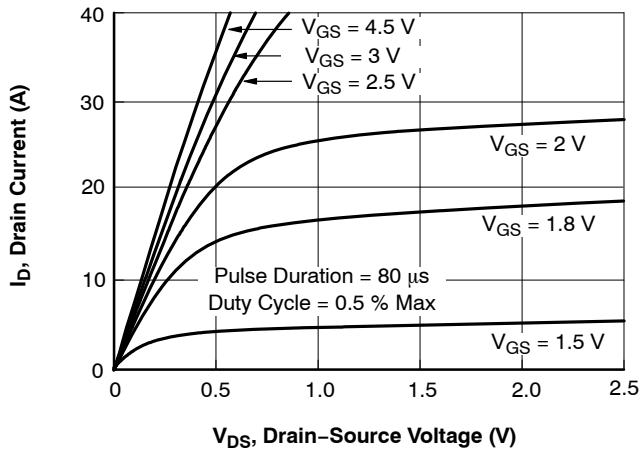


Figure 1. On-Region Characteristics

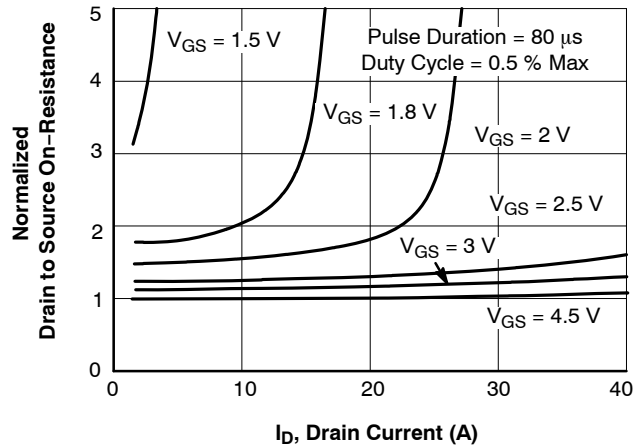


Figure 2. Normalized On-Resistance vs. Drain Current and Gate Voltage

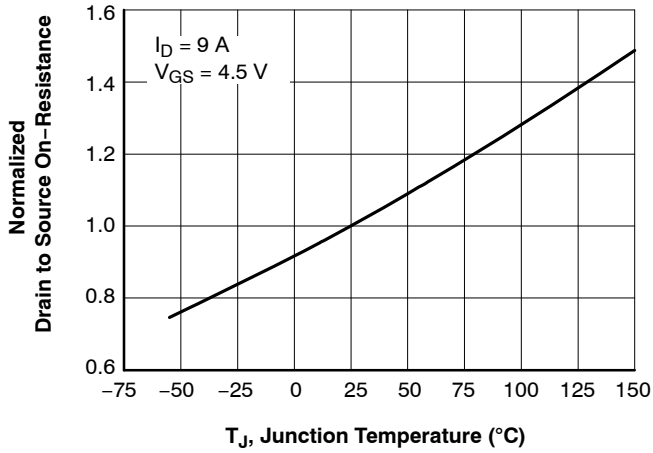


Figure 3. Normalized On-Resistance vs. Junction Temperature

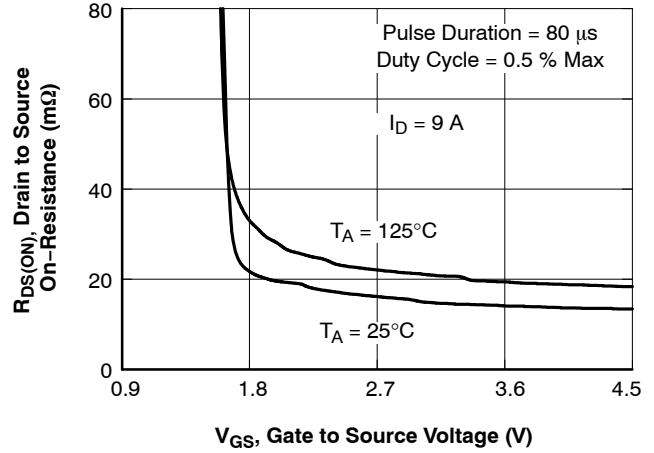


Figure 4. On-Resistance vs. Gate-to-Source Voltage

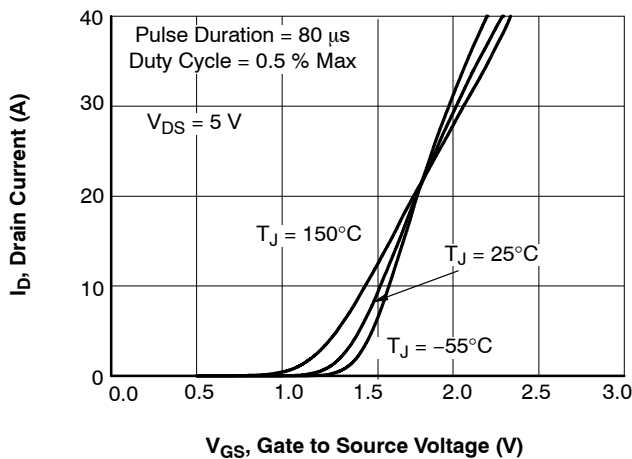


Figure 5. Transfer Characteristics

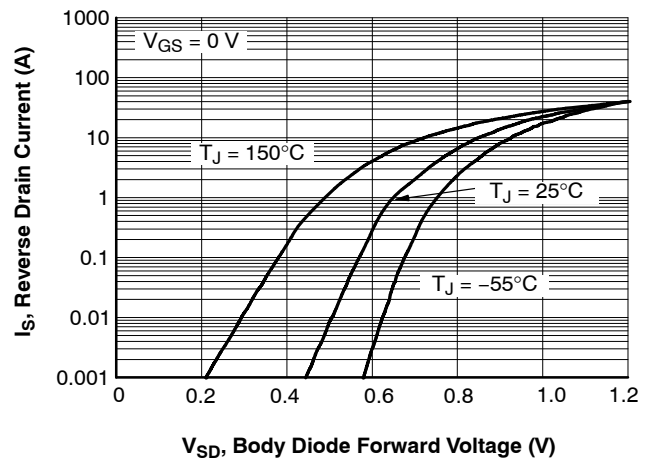


Figure 6. Source to Drain Diode Forward Voltage vs. Source Current

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## TYPICAL CHARACTERISTICS ( $T_J = 25^\circ\text{C}$ , UNLESS OTHERWISE NOTED) (CONTINUED)

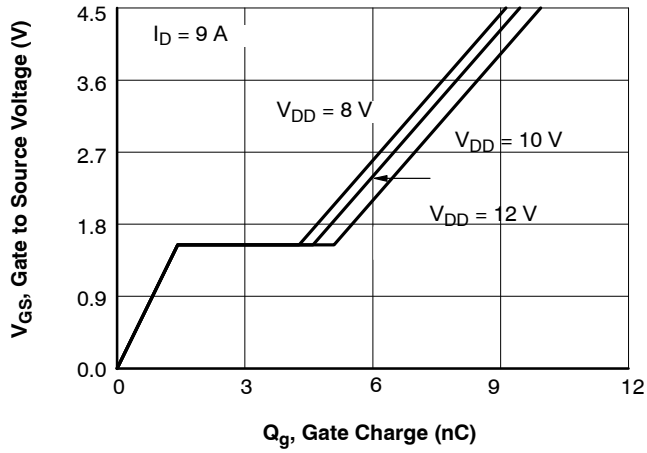


Figure 7. Gate Charge Characteristics

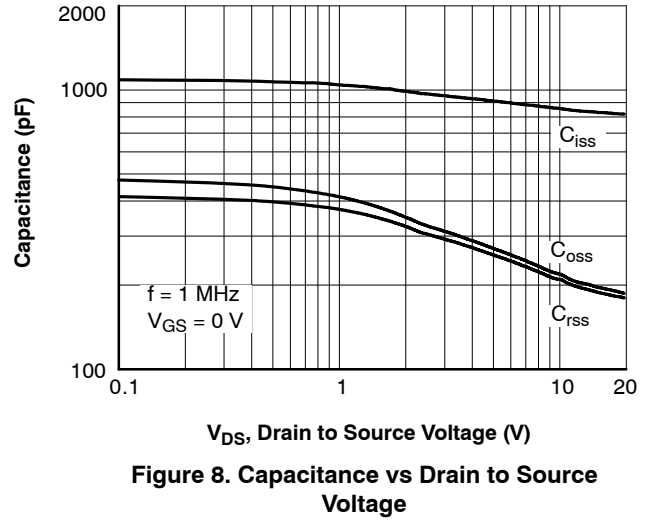


Figure 8. Capacitance vs Drain to Source Voltage

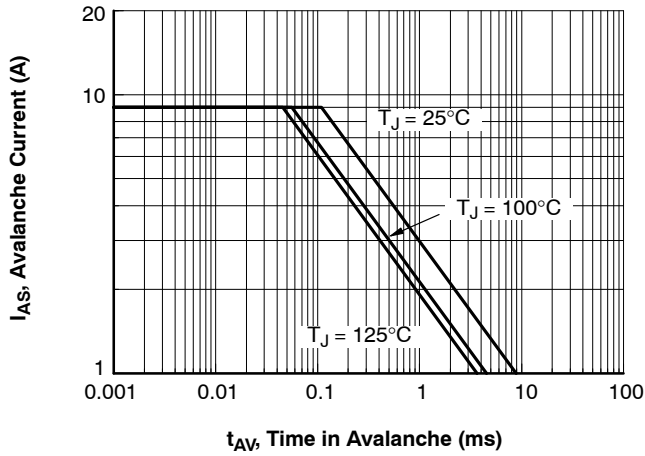


Figure 9. Unclamped Inductive Switching Capability

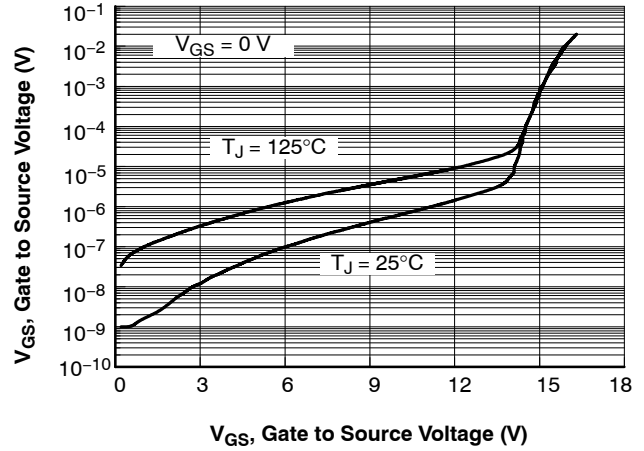


Figure 10. Gate Leakage Current vs Gate to Source Voltage

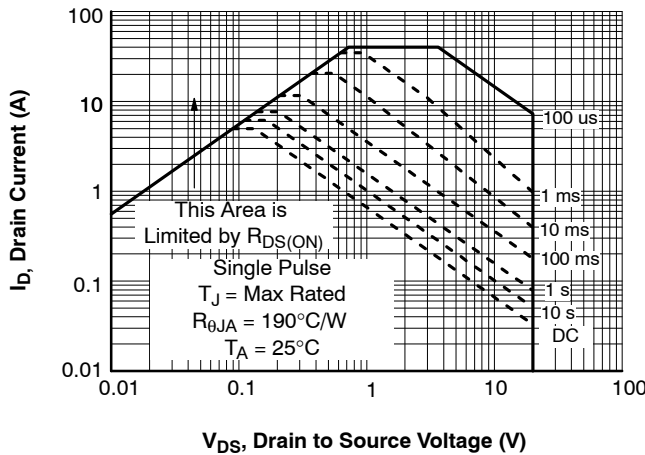


Figure 11. Forward Bias Safe Operating Area

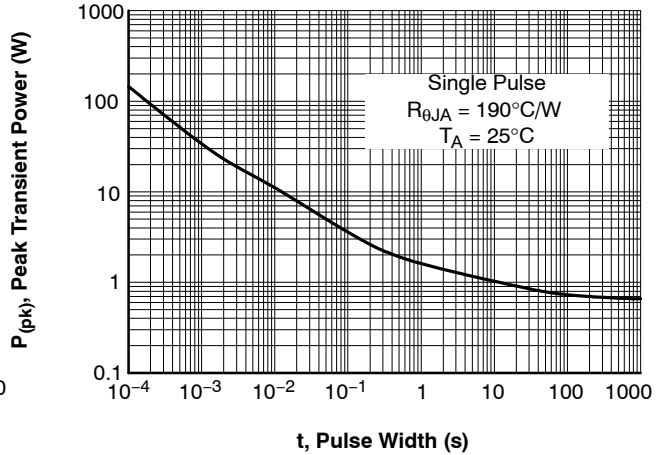


Figure 12. Single Pulse Maximum Power Dissipation

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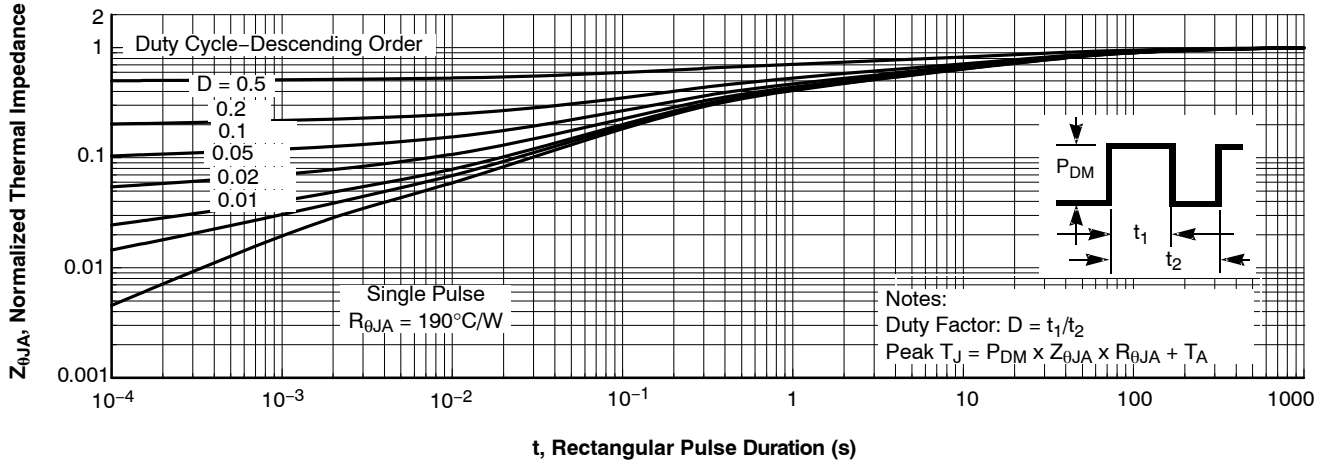


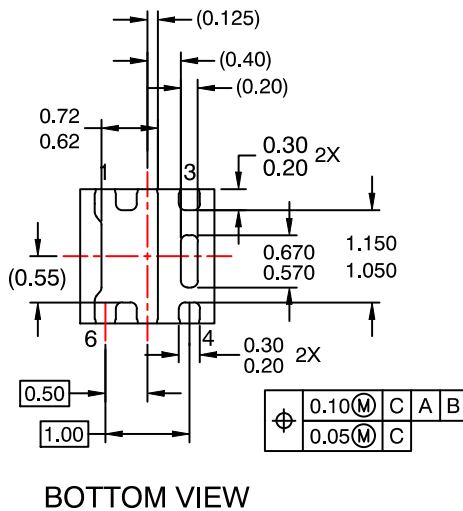
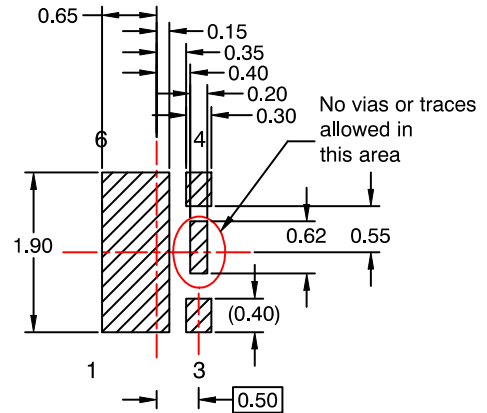
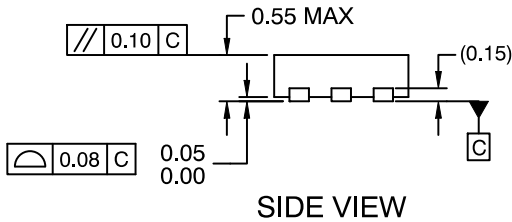
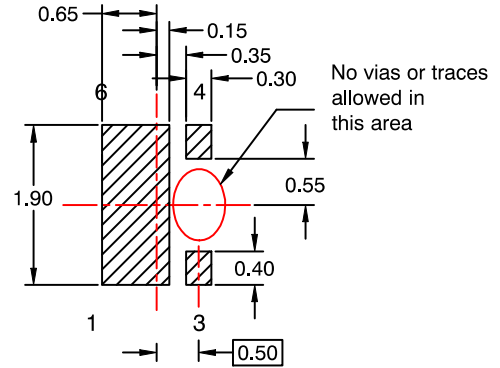
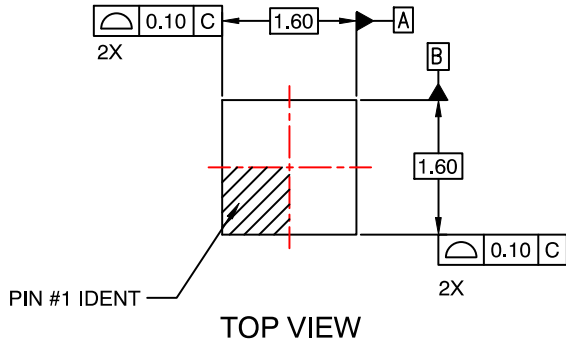
Figure 13. Junction-to-Ambient Transient Thermal Response Curve

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**UDFN6 1.6x1.6, 0.5P**  
**CASE 517DV**  
**ISSUE O**

DATE 31 OCT 2016



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  - B. DIMENSIONS ARE IN MILLIMETERS.
  - C. DIMENSIONS AND TOLERANCES PER ASME Y14.5M, 1994.

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